

(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property
Organization
International Bureau

(43) International Publication Date
19 August 2021 (19.08.2021)



(10) International Publication Number
WO 2021/161117 A1

(51) International Patent Classification:

G11C 11/00 (2006.01) *H01L 45/00* (2006.01)
H01L 21/00 (2006.01) *H01L 27/24* (2006.01)

(21) International Application Number:

PCT/IB2021/050585

(22) International Filing Date:

26 January 2021 (26.01.2021)

(25) Filing Language:

English

(26) Publication Language:

English

(30) Priority Data:

16/789,502 13 February 2020 (13.02.2020) US

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(81) Designated States (unless otherwise indicated, for every kind of national protection available): AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BN, BR, BW, BY, BZ, CA, CH, CL, CN, CO, CR, CU, CZ, DE, DJ, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IR, IS, IT, JO, JP, KE, KG, KH, KN, KP, KR, KW, KZ, LA, LC, LK, LR, LS, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO,

(54) Title: PHASE CHANGE MEMORY USING MULTIPLE STACKS OF PCM MATERIALS

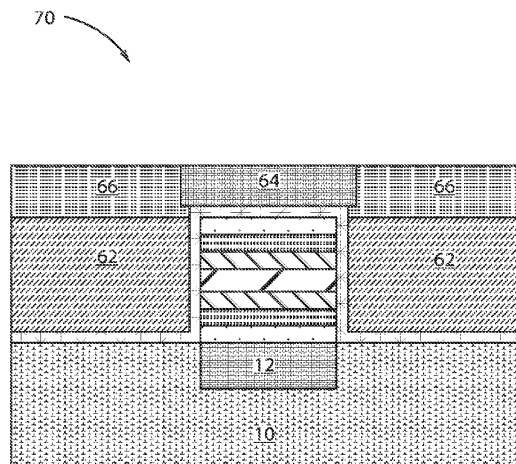


FIG. 11

(57) Abstract: A method is presented for improved linearity of a phase change memory (PCM) cell structure. The method includes forming a bottom electrode (12) over a substrate (10), constructing a PCM stack (20) including a plurality of PCM layers each having a different crystallization temperature over the bottom electrode (12), and forming a top electrode (32) over the PCM stack (20). The crystallization temperature varies in an ascending order from the bottom electrode (12) to the top electrode (32).

[Continued on next page]

NZ, OM, PA, PE, PG, PH, PL, PT, QA, RO, RS, RU, RW,
SA, SC, SD, SE, SG, SK, SL, ST, SV, SY, TH, TJ, TM, TN,
TR, TT, TZ, UA, UG, US, UZ, VC, VN, WS, ZA, ZM, ZW.

(84) Designated States (*unless otherwise indicated, for every kind of regional protection available*): ARIPO (BW, GH, GM, KE, LR, LS, MW, MZ, NA, RW, SD, SL, ST, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, RU, TJ, TM), European (AL, AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, MK, MT, NL, NO, PL, PT, RO, RS, SE, SI, SK, SM, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, KM, ML, MR, NE, SN, TD, TG).

Published:

- *with international search report (Art. 21(3))*
- *in black and white; the international application as filed contained color or greyscale and is available for download from PATENTSCOPE*